



November 1999

FDC637AN Single N-Channel, 2.5V Specified PowerTrench[™] MOSFET

General Description

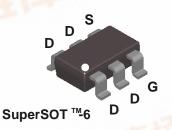
This N-Channel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

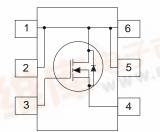
These devices have been designed to offer exceptional power dissipation in a very small footprint compared with bigger SO-8 and TSSOP-8 packages.

Applications

- DC/DC converter
- Load switch
- Battery Protection

- Features
- 6.2 A, 20 V. $R_{DS(on)} = 0.024 \ \Omega @ V_{GS} = 4.5 \ V$ $R_{DS(on)} = 0.032 \ \Omega @ V_{GS} = 2.5 \ V$
- Fast switching speed.
- Low gate charge (10.5nC typical).
- High performance trench technology for extremely low R_{DS(ON)}.
- SuperSOT[™]-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		FDC637AN	Units
/ _{DSS}	Drain-Source Voltage		20	V
V _{GSS}	Gate-Source Voltage		±8	V
I _D	Drain Current - Continuous	(Note 1a)	6.2	A
	Drain Current - Pulsed		20	0250-
P _D	Power Dissipation for Single Operation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

R _{eja}	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R _{ejc}	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.637	637 FDC637AN 7"		8mm	3000 units

Symbol	Parameter	Parameter Test Conditions		Тур	Max	Units
Off Char	acteristics			1		
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	20			V
<u>ΔBV_{DSS}</u> ΔTJ	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$, Referenced to $25^{\circ}C$		14		mV/∘C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 8 V, V_{DS} = 0 V$			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -8 V, V_{DS} = 0 V			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.4	0.82	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D =250µA,Referenced to 125°C		-3		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance			0.019 0.028 0.025	0.024 0.041 0.032	Ω
I _{D(on)}	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	10			А
g _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, \text{ I}_{D} = 6.2 \text{ A}$		7.4		S
Dvnamio	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$		1125		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		290		pF
C _{rss}	Reverse Transfer Capacitance			145		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ A},$	1	9	18	ns
t _r	Turn-On Rise Time	V_{GS} = 4.5 V, R_{GEN} = 6 Ω		13	24	ns
t _{d(off)}	Turn-Off Delay Time			26	42	ns
t _f	Turn-Off Fall Time			11	20	ns
Q _g	Total Gate Charge	$V_{DS} = 5 \text{ V}, \text{ I}_{D} = 6.2 \text{ A},$		10.5	16	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 4.5 V		1.5		nC
Q _{gd}	Gate-Drain Charge			2.2		nC
Drain-Sc	ource Diode Characteristics a	nd Maximum Ratings				
I _s	Maximum Continuous Drain-Source Di	<u> </u>			1.3	A
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_S = 1.3 A$ (Note 2)		0.7	1.2	V

Notes:

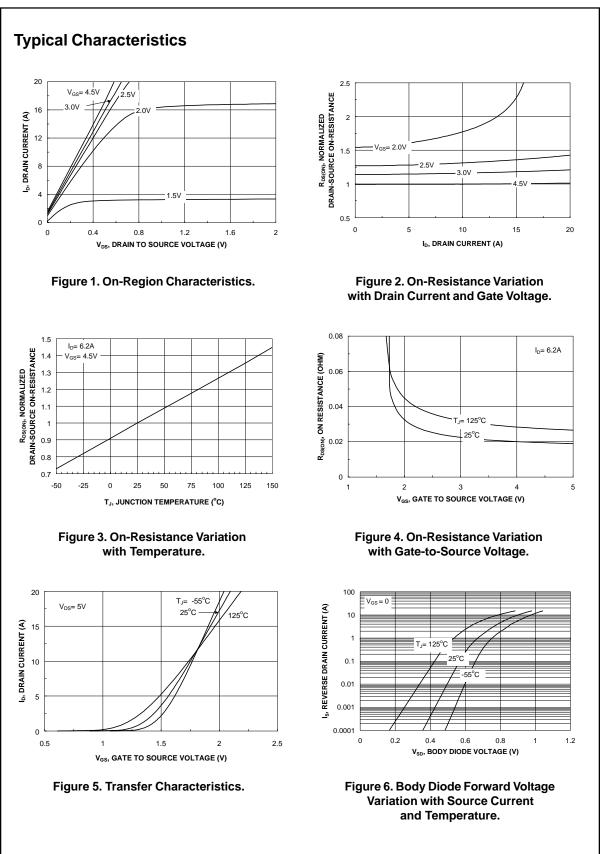
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a) 78° C/W when mounted on a 1.0 in² pad of 2 oz. copper.

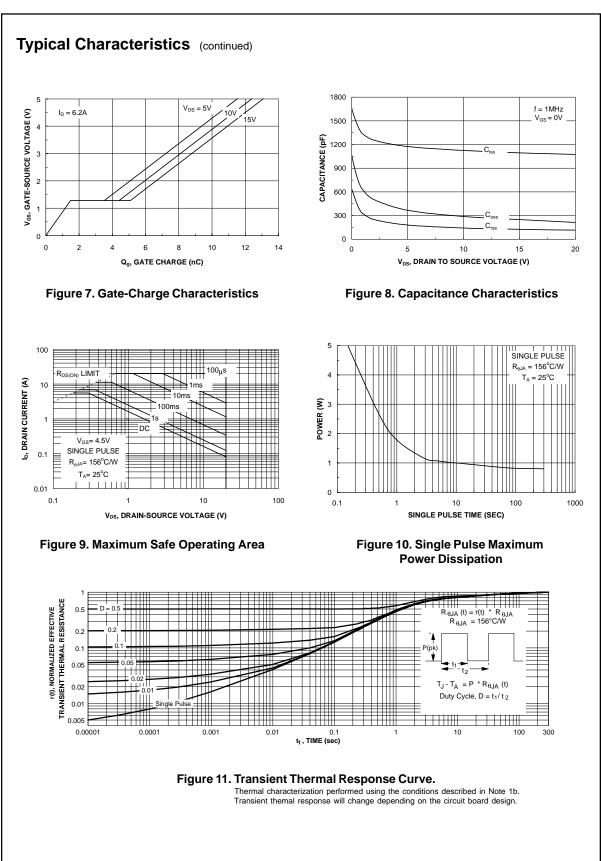
b) 156° C/W when mounted on a minimum pad of 2 oz.copper.

2. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%

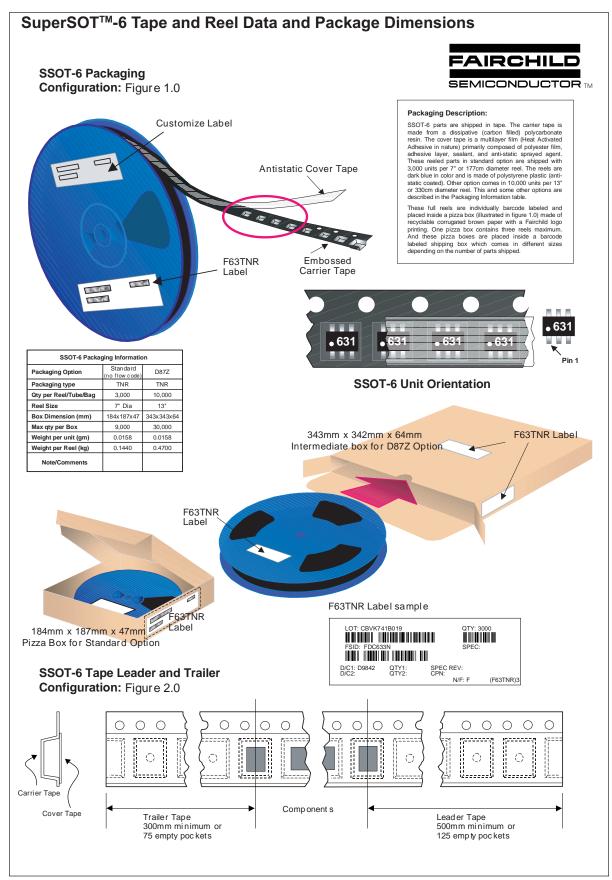
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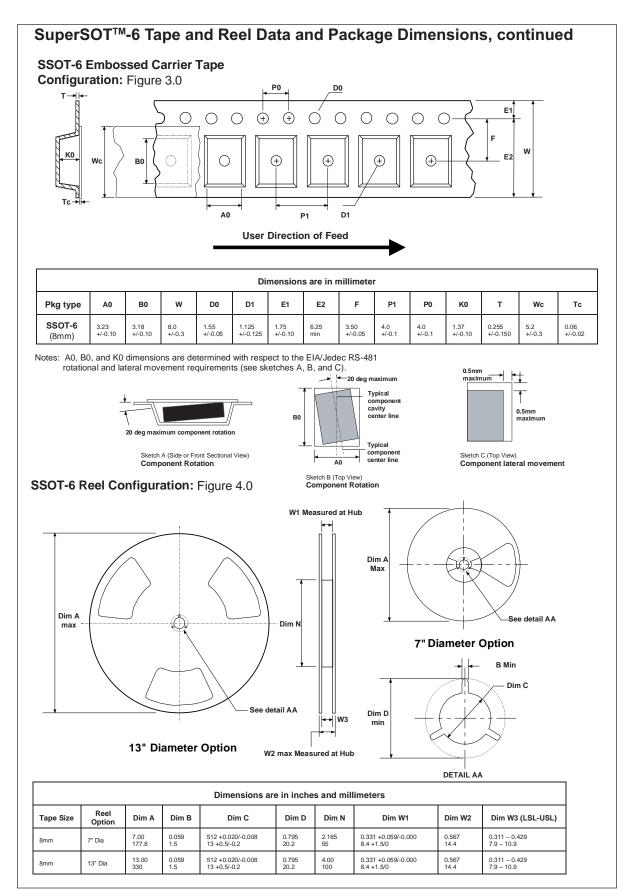


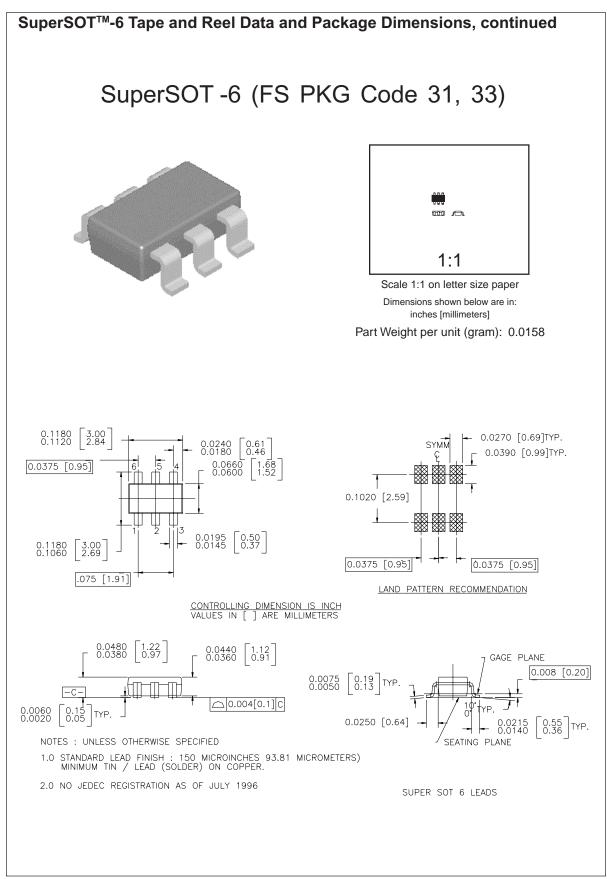
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